

BRIGHT



END-LOOK PACKAGE PIN PHOTO DIODE

● Features

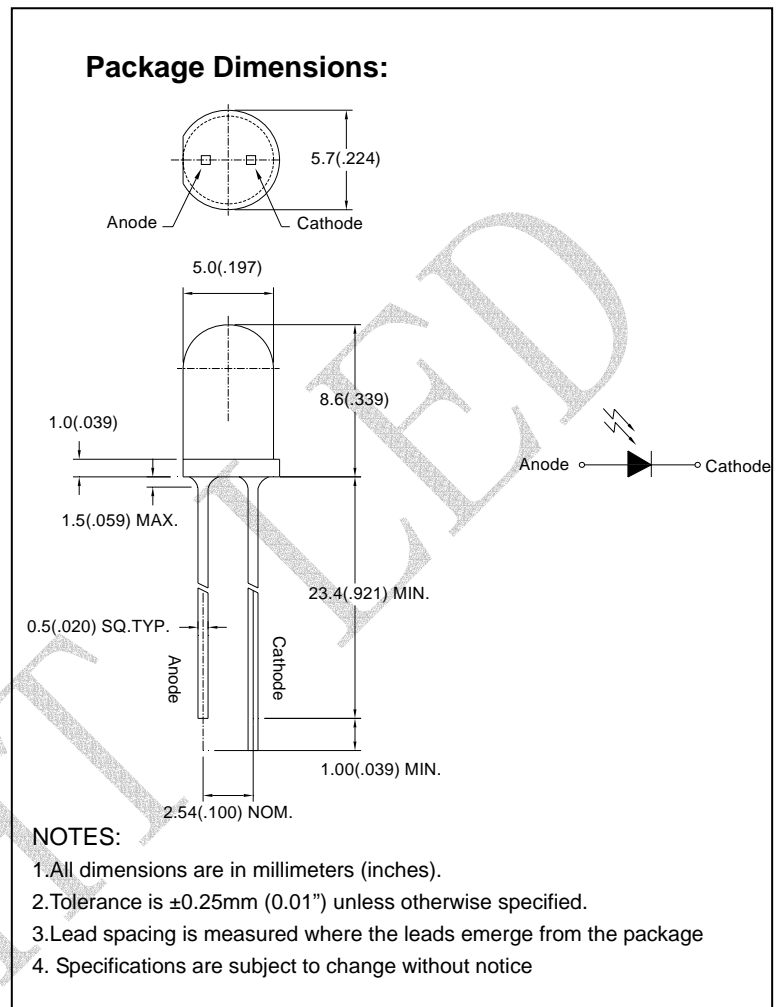
1. Wide receiving angle
2. Linear response vs. irradiance
3. Fast switching time
4. End-looking Package ideal for space limited applications
5. Lens Appearance: Black
6. This product doesn't contain restriction substance, comply RoHS standard

● Description

The BPD-BQDA34 device consists of a PIN silicon photodiode molded in a black epoxy package which allows spectral response from visible to infrared light wavelengths. The wide receiving angle provides relatively even reception over a large area. The end-looking package is designed for easy PC board mounting. This photodiode is mechanically and spectrally matched to BRIGHT's GaAs and GaAlAs series of infrared emitting diodes.

● Absolute Maximum Ratings(Ta=25)

Parameter	Maximum Rating	Unit
Power Dissipation	100	mW
Reverse Breakdown Voltage	60V	
Operating Temperature	-40 ~+85	
Storage Temperature Range	-45 ~+85	

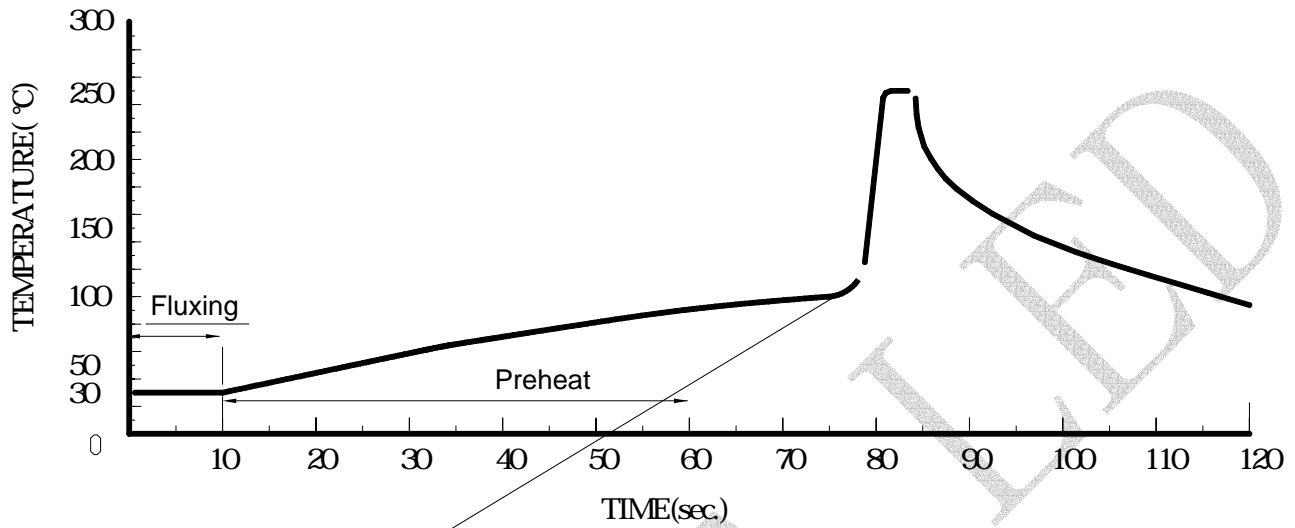




● **Electrical Characteristics** (TA=25 unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Reverse Light Current	I_L	-	80		μA	$V_R=5\text{V}, E_e=1\text{mW}/\text{cm}^2$
Reverse Dark Current	I_D	-	-	100	nA	$V_R=10\text{V}, E_e=0\text{ mW}/\text{cm}^2$
Reverse Break down Voltage	$V_{(BR)}$	35	-	-	-	$I_R=100\mu\text{A}$
Forward Voltage	V_F	0.5	-	1.3	V	$I_F=1\text{mA}$
Total Capacitance	C_T	-	9	-	PF	$V_R=5\text{V}, E_e=0, f=1.0\text{MHZ}$
Rise Time/ Fall Time	tr/ tf	-	50	-	ns	$V_R=20\text{V}, \lambda=940\text{nm}, R_L=50$
Receiving Wavelength	ρ	820	-	1100	nm	

● **Typical Optical-Electrical Characteristic Curves**



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